

Title (en)

COMPOSITION AND METHOD FOR REMOVING ION-IMPLANTED PHOTORESIST

Title (de)

ZUSAMMENSETZUNG UND VERFAHREN ZUR ENTFERNUNG VON IONENIMPLANTIERTEM FOTOLACK

Title (fr)

COMPOSITION ET PROCÉDÉ POUR RETIRER UN PHOTORÉSIST À IMPLANTATION IONIQUE

Publication

**EP 2190967 A4 20101013 (EN)**

Application

**EP 08827598 A 20080820**

Priority

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- US 96545607 P 20070820

Abstract (en)

[origin: WO2009026324A2] A method and mineral acid-containing compositions for removing bulk and/or hardened photoresist material from microelectronic devices have been developed. The mineral acid-containing composition includes at least one mineral acid, at least one sulfur-containing oxidizing agent, and optionally at least one metal ion-containing catalyst. The mineral acid-containing compositions effectively remove the hardened photoresist material while not damaging the underlying silicon-containing layer(s).

IPC 8 full level

**C11D 7/08** (2006.01); **C01B 32/50** (2017.01); **C11D 7/26** (2006.01); **H01L 21/02** (2006.01)

CPC (source: EP US)

**G03F 7/423** (2013.01 - EP US); **H01L 21/31133** (2013.01 - EP US)

Citation (search report)

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- See references of WO 2009026324A2

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